

**Amendments to the Specification:**

Please replace paragraph 0006 at page 2 with the following amended paragraph:

[0006]        In accordance ~~with the purpose of this invention as embodied and broadly described herein~~ one implementation consistent with the principles of the invention, a semiconductor device includes a first fin structure that comprises a dielectric material and includes a first side surface and a second side surface; a second fin structure that comprises a single crystal silicon material and is formed adjacent to the first side surface of the first fin structure; a third fin structure that comprises the single crystal silicon material and is formed adjacent to the second side surface of the first fin structure; a source region that is formed at one end of the first fin structure, the second fin structure, and the third fin structure; a drain region that is formed at an opposite end of the first fin structure, the second fin structure, and the third fin structure; and at least one gate method of manufacturing a semiconductor device that includes a substrate and a dielectric layer formed on the substrate is disclosed. The method includes etching the dielectric layer to form a first fin structure; depositing an amorphous silicon layer; etching the amorphous silicon layer to form a second fin structure adjacent a first side surface of the first fin structure and a third fin structure adjacent a second, opposite side surface of the first fin structure; depositing a metal layer on at least upper surfaces of the second fin structure and the third fin structure; performing a metal-induced crystallization operation to convert the amorphous silicon in the second and third fin structures to a single-crystal silicon material; forming a source region and a drain region; depositing a gate material

over the first, second, and third fin structures; and patterning and etching the gate material to form at least one gate electrode.

Please replace paragraph 0007 beginning on page 2 with the following amended paragraph:

[0007] In another implementation consistent with the present invention, a method of manufacturing a semiconductor device that includes a substrate and a dielectric layer formed on the substrate is disclosed. The method includes etching the dielectric layer to form a first fin structure; depositing an amorphous silicon layer; etching the amorphous silicon layer to form a second fin structure adjacent a first side surface of the first fin structure and a third fin structure adjacent a second, opposite side surface of the first fin structure; depositing a metal layer on at least upper surfaces of the second fin structure and the third fin structure; performing a metal-induced crystallization operation to convert the amorphous silicon in the second and third fin structures to a single-crystal silicon material; forming a source region and a drain region; depositing a gate material over the first, second, and third fin structures; and patterning and etching the gate material to form at least one gate electrode for forming fin structures for a semiconductor device is provided. The method includes forming a first fin structure including a dielectric material and including a first side surface and a second side surface; forming a second fin structure adjacent the first side surface of the first fin structure; and forming a third fin structure adjacent the second side surface of the first fin structure, where the

second fin structure and the third fin structure are formed of a different material than the first fin structure.

Please replace paragraph 0008 at page 3 with the following amended paragraph:

[0008] In yet another implementation consistent with the principles of the invention, ~~a semiconductor device that includes a first fin structure, a second fin structure, and a third fin structure is disclosed. The first and second fin structures include a single crystal silicon material. The third fin structure is located between the first fin structure and the second fin structure and includes a dielectric material. The third fin structure causes stress to be induced in the single crystal silicon material of the first fin structure and the second fin structure~~ method for forming fin structures for a semiconductor device that includes a substrate and a dielectric layer formed on the substrate is provided. The method includes etching the dielectric layer to form a first fin structure; depositing an amorphous silicon layer; and etching the amorphous silicon layer to form a second fin structure adjacent a first side surface of the first fin structure and a third fin structure adjacent a second, opposite side surface of the first fin structure.